

November 2013

# FDD6N50 / FDU6N50 N-Channel UniFET<sup>TM</sup> MOSFET 500 V, 6 A, 900 m $\Omega$

#### **Features**

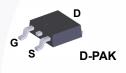
- $R_{DS(on)}$  = 900 m $\Omega$  (Max.) @  $V_{GS}$  = 10 V,  $I_D$  = 3 A
- Low Gate Charge (Typ. 12.8 nC)
- Low C<sub>rss</sub> (Typ. 9 pF)
- · 100% Avalanche Tested
- Improved dv/dt Capability

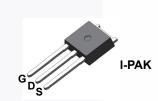
### **Applications**

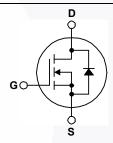
- LCD/LED/PDP TV
- Lighting
- · Uninterruptible Power Supply
- AC-DC Power Supply

# **Description**

UniFET<sup>TM</sup> MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.







# **Absolute Maximum Ratings** $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol		Parameter		FDD6N50TM / FDD6N50TM_WS / FDU6N50TU	Unit
V <sub>DSS</sub>	Drain-Source Voltage			500	V
I <sub>D</sub>	Drain Current	- Continuous (T <sub>C</sub> = 25°C) - Continuous (T <sub>C</sub> = 100°C)		6 3.8	A A
I <sub>DM</sub>	Drain Current	- Pulsed	(Note 1)	24	Α
V <sub>GSS</sub>	Gate-Source voltage			±30	V
E <sub>AS</sub>	Single Pulsed Avalanche Energy		(Note 2)	270	mJ
I <sub>AR</sub>	Avalanche Current		(Note 1)	6	Α
E <sub>AR</sub>	Repetitive Avalanche Energy		(Note 1)	8.9	mJ
dv/dt	Peak Diode Recovery dv/dt		(Note 3)	4.5	V/ns
$P_{D}$	Power Dissipation	(T <sub>C</sub> = 25°C) - Derate Above 25°C		89 0.71	W W/°C
T <sub>J,</sub> T <sub>STG</sub>	Operating and Storage Temperature Range			-55 to +150	°C
T <sub>L</sub>	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds			300	°C

#### **Thermal Characteristics**

Symbol	Parameter	FDD6N50TM / FDD6N50TM_WS / FDU6N50TU	Unit	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	1.4	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	83		

# **Package Marking and Ordering Information**

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDD6N50TM	FDD6N50	DPAK	Tape and Reel	330 mm	16 mm	2500 units
FDD6N50TM_WS	FDD6N50S	DPAK	Tape and Reel	330 mm	16 mm	2500 units
FDU6N50TU	FDU6N50	IPAK	Tube	N/A	N/A	75 units

# **Electrical Characteristics** $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Тур.	Max	Unit
Off Charac	cteristics				•	•
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage $V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		500			V
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250 μA, Referenced to 25°C		0.5		V/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{DS} = 500 \text{ V}, V_{GS} = 0 \text{ V}$ $V_{DS} = 400 \text{ V}, T_{C} = 125^{\circ}\text{C}$			1 10	μA μA
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 30 V, V <sub>DS</sub> = 0 V			100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = -30 V, V <sub>DS</sub> = 0 V			-100	nA
On Charac	teristics					•
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	3.0		5.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 3 A		0.76	0.9	Ω
9 <sub>FS</sub>	Forward Transconductance $V_{DS} = 40 \text{ V}, I_{D} = 3 \text{ A}$			2.5		S
Dynamic C	Characteristics					
C <sub>iss</sub>	Input Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$		720	940	pF
C <sub>oss</sub>	Output Capacitance	f = 1.0 MHz		95	190	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			9	13.5	pF
Switching	Characteristics					
t <sub>d(on)</sub>	Turn-On Delay Time	$V_{DD} = 250 \text{ V}, I_D = 6 \text{ A},$		6	20	ns
t <sub>r</sub>	Turn-On Rise Time	$V_{GS}$ = 10 V, $R_G$ = 25 $\Omega$		55	120	ns
t <sub>d(off)</sub>	Turn-Off Delay Time			25	60	ns
t <sub>f</sub>	Turn-Off Fall Time	(Note 4)	/	35	80	ns
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> = 400 V, I <sub>D</sub> = 6 A,		12.8	16.6	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>GS</sub> = 10 V	/	3.7		nC
Q <sub>gd</sub>	Gate-Drain Charge	(Note 4)		5.8		nC
Drain-Sou	rce Diode Characteristics and Maximun	n Ratings				ı
I <sub>S</sub> Maximum Continuous Drain-Source Diode Forward Current					6	Α
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward Current				24	Α
$V_{SD}$	Drain-Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 6 A			1.4	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 6 A,		275	/	ns
Q <sub>rr</sub>	Reverse Recovery Charge	dl <sub>F</sub> /dt =100 A/μs		1.7		μС

#### Notes

<sup>1.</sup> Repetitive rating: pulse-width limited by maximum junction temperature.

<sup>2.</sup> I $_{AS}$  = 6 A, V $_{DD}$  = 50 V, L=13.5 mH, R $_{G}$  = 25  $\Omega$ , starting T $_{J}$  = 25°C.

<sup>3.</sup> I  $_{SD}$   $\leq$  6 A, di/dt  $\leq$  200 A/µs, V  $_{DD}$   $\leq$  BV  $_{DSS}$  , starting T  $_{J}$  = 25°C.

<sup>4.</sup> Essentially independent of operating temperature typical characteristics.

# **Typical Performance Characteristics**

Figure 1. On-Region Characteristics

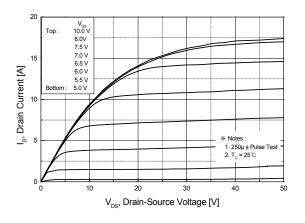


Figure 3. On-Resistance Variation vs.
Drain Current and Gate Voltage

Figure 2. Transfer Characteristics

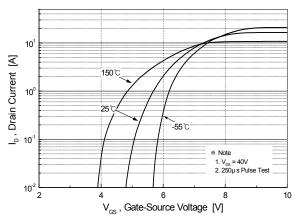


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

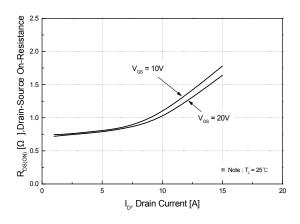
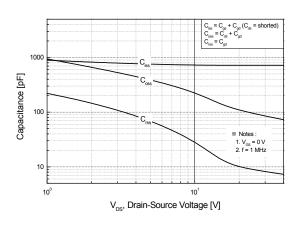


Figure 5. Capacitance Characteristics



E 10<sup>1</sup>

10<sup>2</sup>

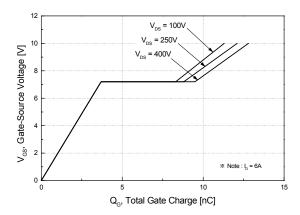
10<sup>3</sup>

10<sup>3</sup>

150 C 25 C

11.0<sub>m</sub> = Notes:
1.0<sub>m</sub> = Source Drain Voltage [V]

Figure 6. Gate Charge Characteristics



# **Typical Performance Characteristics** (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

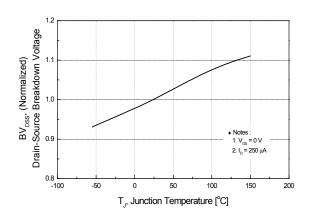


Figure 8. On-Resistance Variation vs. Temperature

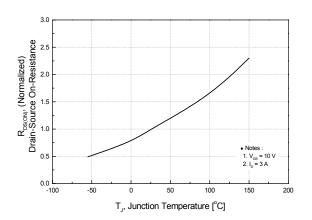


Figure 9. Maximum Safe Operating Area

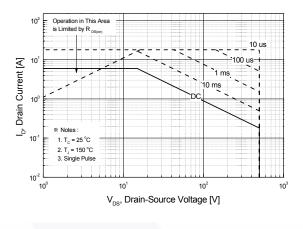


Figure 10. Maximum Drain Current vs. Case Temperature

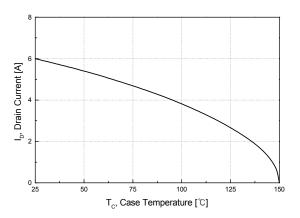
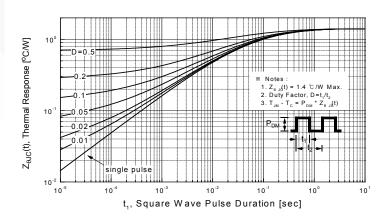


Figure 11. Transient Thermal Response Curve



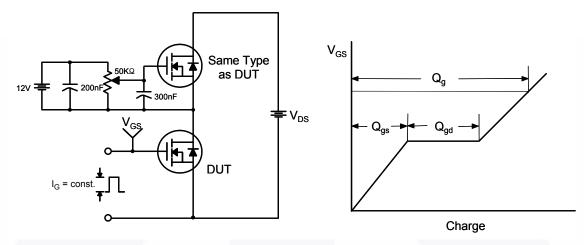


Figure 12. Gate Charge Test Circuit & Waveform

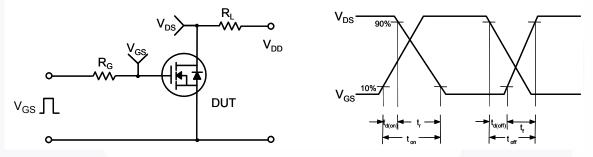


Figure 13. Resistive Switching Test Circuit & Waveforms

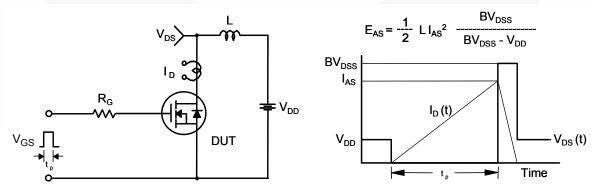


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

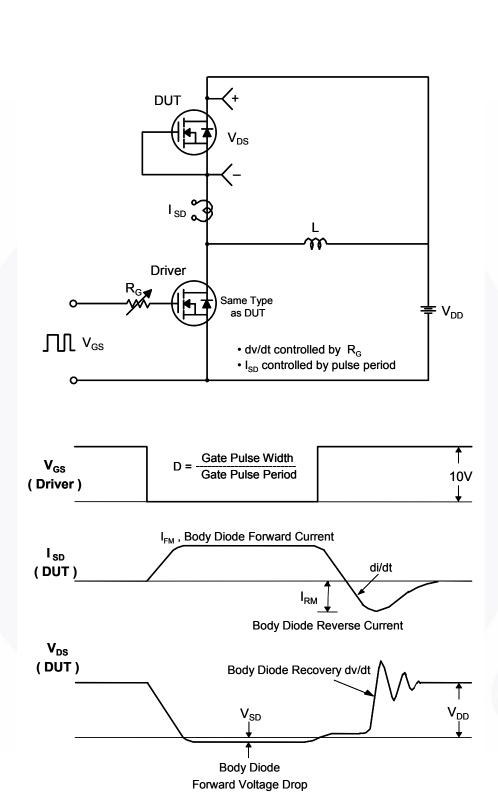


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

#### **Mechanical Dimensions**

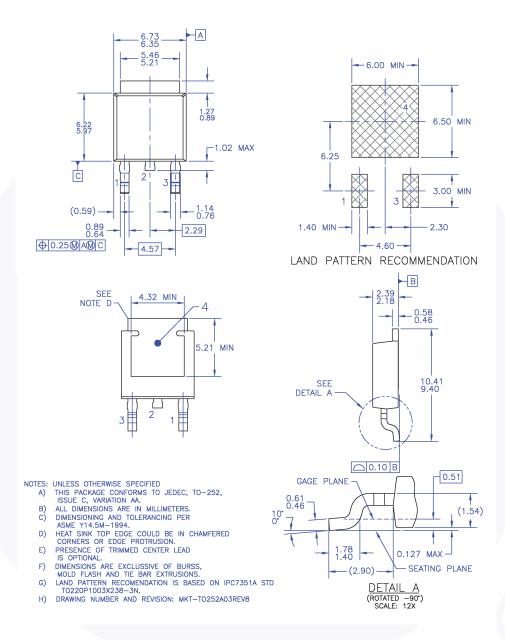


Figure 16. TO252 (D-PAK), Molded, 3-Lead, Option AA&AB

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#### **Mechanical Dimensions**

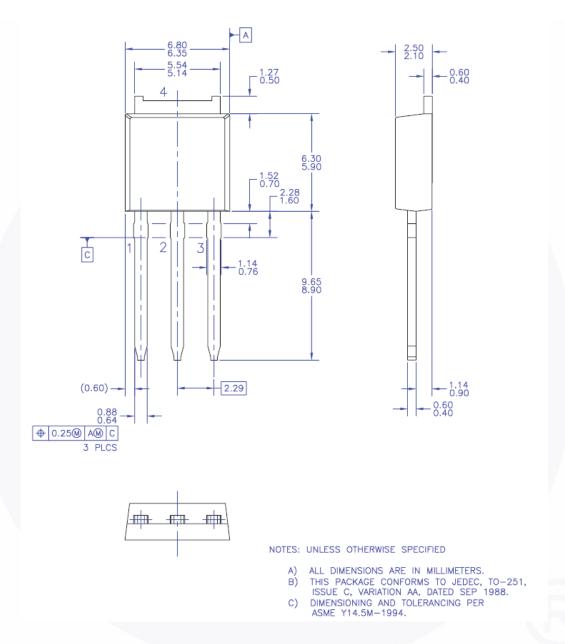


Figure 17. TO-251 (I-PAK), Molded, 3-Lead, Option AA

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